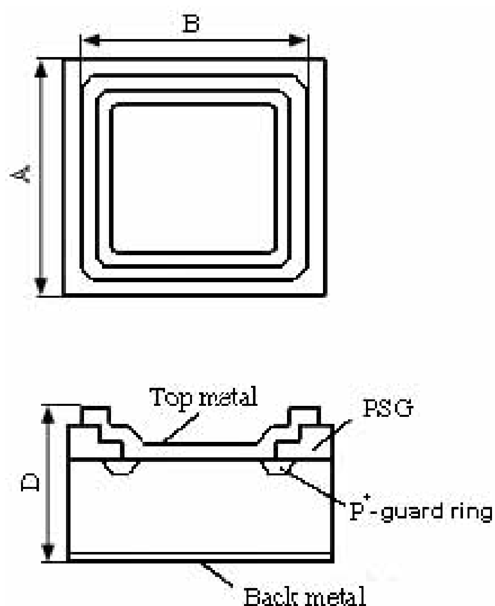
Dec. 2010

SCHOTTKY DIODES KD 2909S6.

PRELIMINARY

VSP-MIKRON	1A/200V. Die Size-35mil.			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	200	210
Average Rectified Forward Current	$I_{F(AV)}$	A	1,0	-
DC Forward Voltage @ 25˚C, I_F=1,0A	V_F	V	0,89	0,87
Maximum Reverse Current @ 25˚C, V_R=200V 125˚C, V_R=200V	I_R	mA	0,005 5,0	0,003 4,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	30	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<175˚C.	I_{RRM}	A	0,8	
Reverse Recovery Time, I_F=1A, V_R=30V, dI_F/dt=100A/uS.	t_{rr}	nS	35	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	V_{ESD}	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	175	



DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	900 900
B_X B_y	Top Metal Size	760 760
D	Thickness	300max.
Scribe line Width		80

Top metal: a)***Al-Ni-Ag*** – for Soldering;

b)***Al*** – for Wire Bonding.

Backside metal: ***Ti-Ni-Ag***.

www.vsp-mikron.com